



APT33N90JCU3 Information



For Reference Only

Part Number APT33N90JCU3

Manufacturer Microsemi Corporation

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 900V 33A SOT227

Package SOT-227-4, miniBLOC

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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APT33N90JCU3 Specifications

Manufacturer Part NumberAPT33N90JCU3ManufacturerMicrosemi CorporationCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageSOT-227-4, miniBLOCSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)900VCurrent - Continuous Drain (Id) @ 25°C33ADrive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 3mAGate Charge (Qg) (Max) @ Vgs270nC @ 10VInput Capacitance (Ciss) (Max) @ Vds6800pF @ 100VVgs (Max)±20VFET FeatureSuper JunctionPower Dissipation (Max)290W (Tc)Rds On (Max) @ Id, Vgs120 mOhm @ 26A, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeChassis Mount		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single SOT-227-4, miniBLOC Series FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Ourrent - Continuous Drain (Id) @ 25°C 33A Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 120 mOhm @ 26A, 10V Operating Temperature	Manufacturer Part Number	APT33N90JCU3
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FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 33A Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Super Junction Power Dissipation (Max) Que Vgs 120 mOhm @ 26A, 10V Operating Temperature	Package	SOT-227-4, miniBLOC
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Drain to Source Voltage (Vdss) 900V Current - Continuous Drain (Id) @ 25°C 33A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 3mA Gate Charge (Qg) (Max) @ Vgs 270nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 6800pF @ 100V Vgs (Max) ±20V FET Feature Super Junction Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 26A, 10V Operating Temperature -40°C ~ 150°C (TJ)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 33A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 3mA Gate Charge (Qg) (Max) @ Vgs 270nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 6800pF @ 100V Vgs (Max) ±20V FET Feature Super Junction Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 26A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 3mA Gate Charge (Qg) (Max) @ Vgs 270nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 6800pF @ 100V Vgs (Max) ±20V FET Feature Super Junction Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 26A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Drain to Source Voltage (Vdss)	900V
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Gate Charge (Qg) (Max) @ Vgs 270nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 6800pF @ 100V Vgs (Max) ±20V FET Feature Super Junction Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 26A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds	Vgs(th) (Max) @ Id	3.5V @ 3mA
Vgs (Max) $\pm 20 \text{V}$ FET FeatureSuper JunctionPower Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs $120 \text{ mOhm } @ 26 \text{A}, 10 \text{V}$ Operating Temperature $-40 ^{\circ}\text{C} \sim 150 ^{\circ}\text{C (TJ)}$	Gate Charge (Qg) (Max) @ Vgs	270nC @ 10V
FET Feature Super Junction Power Dissipation (Max) Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 26A, 10V Operating Temperature -40°C ~ 150°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	6800pF @ 100V
Power Dissipation (Max) 290W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 26A, 10V Operating Temperature $-40^{\circ}\text{C} \sim 150^{\circ}\text{C}$ (TJ)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 120 mOhm @ 26A, 10V Operating Temperature -40°C ~ 150°C (TJ)	FET Feature	Super Junction
Operating Temperature $-40^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Power Dissipation (Max)	290W (Tc)
	Rds On (Max) @ Id, Vgs	120 mOhm @ 26A, 10V
Mounting Type Chassis Mount	Operating Temperature	-40°C ~ 150°C (TJ)
	Mounting Type	Chassis Mount
Supplier Device Package SOT-227	Supplier Device Package	SOT-227
Package / Case SOT-227-4, miniBLOC	Package / Case	SOT-227-4, miniBLOC
Report errors?		Report errors?

APT33N90JCU3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

APT33N90JCU3 Payment Methods



















APT33N90JCU3 Shipping Methods













If you have any question about APT33N90JCU3, please do not hesitate to contact us!

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